



74LVC1G17

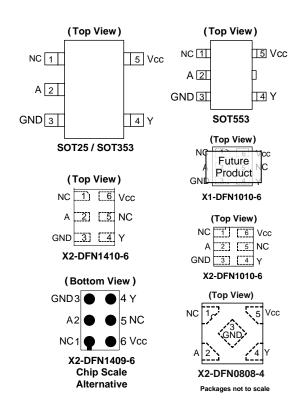
SINGLE SCHMITT-TRIGGER BUFFER

Description

The 74LVC1G17 is a single 1-input Schmitt-trigger buffer with a standard push-pull output. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

$$\mathsf{Y} = \mathsf{A}$$

Pin Assignments



Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115)
 - 2,000-V Human Body Model (A114)
 - Latch-Up Exceeds 100mA per JESD 78, Class I
- Range of Package Options
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

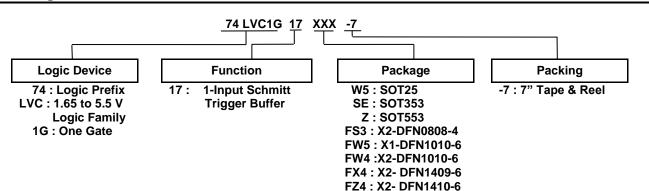
- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and < 1000 ppm antimony compounds.



Ordering Information



Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4, 5)	Size	Quantity	Part Number Suffix
74LVC1G17W5-7	W5	SOT25	3.0mm X 2.8mm X 1.2mm 0.95 mm lead pitch	3,000/Tape & Reel	-7
74LVC1G17SE-7	SE	SOT353	2.0mm X 2.0mm X 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74LVC1G17Z-7	Z	SOT553	1.1.6mm X 1.6 mm X 0.62mm 0.5 mm lead pitch	4,000/Tape & Reel	-7
74LVC1G17FS3-7	FS3	X2-DFN0808-4	0.9mm X 0.9 mm X 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74LVC1G17FW5-7 (Future Product)	FW5	X1-DFN1010-6 (Future Product)	1.0mm X 1.0mm X 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74LVC1G17FW4-7	FW4	X2-DFN1010-6	1.0mm X 1.0mm X 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74LVC1G17FX4-7	FX4	X2-DFN1409-6 (Chip Scale Alternative)	1.4mm X 0.9mm X 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74LVC1G17FZ4-7	FZ4	X2-DFN1410-6	1.4mm X 1.0mm X 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

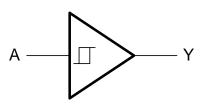
Notes:

4. Pad layout as shown on Diodes' suggested pad layout, which can be found on our website at http://www.diodes.com/package-outlines.html. 5. The taping orientation is located on our website at https://www.diodes.com/assets/Diodes-Packaging/ap02007.pdf.

Pin Descriptions

Pin Name	Description
А	Data Input
GND	Ground
Y	Data Output
V _{CC}	Supply Voltage

Logic Diagram



Function Table

Inputs	Output
Α	Y
Н	Н
L	L



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage Applied to Output in High Impedance or IOFF State	-0.5 to 6.5	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
l _{iK}	Input Clamp Current V _I < 0	-50	mA
Ι _{ΟΚ}	Output Clamp Current	-50	mA
lo	Continuous Output Current	±50	mA
I _{CC} , I _{GND}	Continuous Current through V _{CC} or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes:

6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range..

Recommended Operating Conditions (Note 8)

Symbol		Parameter	Min	Max	Unit	
N/		Operating	1.65	5.5	V	
V _{CC}	Operating Voltage	Data retention only	1.5	_	V	
VI	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V _{CC}	V	
		$V_{CC} = 1.65 V$	_	-4		
		$V_{CC} = 2.3V$	_	-8		
		V _{CC} = 2.7V	_	-12	.	
I _{OH}	High-Level Output current		_	-16	mA	
		$V_{CC} = 3V$	_	-24]	
		$V_{CC} = 4.5V$	_	-32		
		V _{CC} = 1.65V	_	4		
		$V_{CC} = 2.3V$	_	8		
		V _{CC} = 2.7V	_	12		
I _{OL}	Low-Level Output current		_	16	mA	
		$V_{CC} = 3V$	_	24		
		$V_{CC} = 4.5V$	_	32]	
T _A	Operating Free-Air Temperature	_	-40	+125	°C	

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics $T_A = -40^{\circ}C$ to $+85^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Мах	Unit	
		_	1.65V	0.70	_	1.20	_	
		—	2.3V	1.11	_	1.60	_	
V_{T+}		—	3V	1.50	_	2.00	_	
	i nresnoid voltage	_	4.5V	2.16	_	2.74	_	
		—	5.5V	2.61	_	3.33	_	
		—	1.65V	0.30	_	0.72	_	
		—	2.3V	0.58	_	1.00	_	
VT-		_	3V	0.80	_	1.30	_	
	i nresnoid voltage	_	4.5V	1.21	_	1.95	_	
	Positive-going Input Threshold Voltage Negative-going Input Threshold Voltage Hysteresis (VT+ - VT-) High Level Output Voltage Low-Level Output Voltage Input Current Power Down Leakage Current	—	5.5V	1.45	_	2.35	_	
		—	1.65V	0.30	_	0.62	_	
		—	2.3V	0.40	_	0.80	_	
ΔV_T		—	3V	0.35	_	1.00	_	
	(V _{T+} - V _{T-})	—	4.5V	0.55	_	1.10	_	
		_	5.5V	0.60	_	1.20	_	
		I _{OH} = -100µА	1.65V to 5.5V	Vcc - 0.1	_	_		
		I _{OH} = -4mA	1.65V	1.2	_	_		
		I _{OH} = -8mA	2.3V	1.9	_	_		
Vон	High Level Output Voltage	I _{OH} = -12mA	2.7V	2.2	_	_	V	
		I _{OH} = -16mA		2.4	_	_		
		I _{OH} = -24mA	- 3V	2.3	_			
		I _{OH} = -32mA	4.5V	3.8	_	_		
		I _{OL} = 100μΑ	1.65V to 5.5V	_	_	0.1		
		I _{OL} = 4mA	1.65V	_	_	0.45		
		I _{OL} = 8mA	2.3V	_	_	0.3		
Vol	Low-Level Output Voltage	$I_{OL} = 12mA$	2.7V	_	_	0.4	V	
		I _{OL} = 16mA		_	_	0.4		
		$I_{OL} = 24mA$	- 3V	_	_	0.55	1	
		$I_{OL} = 32 \text{mA}$	4.5V	_	_	0.55	1	
lı –	Input Current	V _I = 5.5 V or GND	0 to 5.5V	_	_	± 5	μA	
IOFF	Power Down Leakage Current	V_{I} or $V_{O} = 5.5V$	0	_	_	± 10	μA	
lcc	Supply Current	$V_{I} = 5.5V$ of GND $I_{O} = 0$	1.65V to 5.5V	_	_	10	μA	
Δlcc	Additional Supply Current	Input at V _{CC} –0.6V	3V to 5.5V	_	_	500	μA	



Electrical Characteristics (@T_A = -40°C to +125°C. All typical values are at V_{CC} = 3.3V, T_A = +25°C)

Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур.	Max	Unit	
		_	1.65V	0.70	_	1.20	_	
		_	2.3V	1.11	_	1.60	_	
V _{T+}	Positive-Going Input	_	3 V	1.50	_	2.00	_	
	Threshold Voltage	_	4.5V	2.16	_	2.74	_	
		_	5.5V	2.61		3.33	_	
			1.65V	0.30		0.75		
			2.3V	0.58		1.03		
V _T -	Negative-Going Input Threshold Voltage		3V	0.80		1.33		
	Theshold voltage		4.5V	1.21		1.95		
			5.5V	1.45		2.35		
		_	1.65V	0.30		0.62	_	
		_	2.3V	0.37		0.80	_	
ΔV_T	Hysteresis (V _{T+} - V _{T-})		3V	0.32		1.00		
	(VT+- VT-)		4.5V	0.50		1.20		
		_	5.5V	0.55		1.40	_	
		I _{OH} = -100µА	1.65V to 5.5V	V _{CC} -0.1	_	_		
		I _{OH} = -4mA	1.65V	0.95	_	_		
		I _{OH} = -8mA	2.3V	1.7		—		
Vон	High Level Output Voltage	I _{OH} = -12mA	2.7V	1.9	_	_	V	
		I _{OH} = -16mA	0)/	2.2	_	_		
		I _{OH} = -24mA	- 3V	2.0		_		
		I _{OH} = -32mA	4.5V	3.4	_	_		
		I _{OL} = 100μA	1.65V to 5.5V	—		0.1		
		$I_{OL} = 4mA$	1.65V	—	_	0.7		
		I _{OL} = 8mA	2.3V	—		0.45		
Vol	High-Level Input Voltage	$I_{OL} = 12mA$	2.7V	—		0.6	V	
		I _{OL} = 16mA	2)/	—		0.6		
		$I_{OL} = 24mA$	- 3V	—		0.8		
		$I_{OL} = 32mA$	4.5V	—		0.8		
lı –	Input Current	$V_I = 5.5 \text{ V or GND}$	0 to 5.5V	—	_	± 100	μA	
IOFF	Power Down Leakage Current	V_{I} or $V_{O} = 5.5V$	0	_	_	± 200	μA	
Icc	Supply Current	$V_I = 5.5V$ of GND $I_O = 0$	1.65V to 5.5V		_	200	μA	
ΔIcc	Additional Supply Current	Input at V _{CC} – 0.6 V	3V to 5.5V	_	_	5,000	μA	



Package Characteristics (All typical values are at V_{CC} = 3.3V, T_A = +25°C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
		SOT25		—	204	_	
		SOT353		_	371	_	
		SOT553		—	231		
0	θ _{JA} Thermal Resistance Junction-to-Ambient	X2-DFN0808-4		—	400		0000
ÐJA		X1-DFN1010-6	(Note 9)	—	435		°C/W
		X2-DFN1010-6		—	445		
		X2-DFN1409-6		—	470		
		X2-DFN1410-6		—	460		
		SOT25		—	52		-
		SOT353		—	143		
		SOT553		—	105		
0	Thermal Resistance	X2-DFN0808-4		—	225		
θ」С	Junction-to-Case	X1-DFN1010-6	(Note 9)	—	250		°C/W
		X2-DFN1010-6		_	250	_	
		X2-DFN1409-6]	_	275	_	
		X2-DFN1410-6			265	_	

Note: 9. Test condition for each of the 8 package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

 T_A = -40°C to +85°C, C_L = 15pF as noted (See Figure 1)

Parameter	From Input	To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
			Min	Max	Min	Max	Min	Max	Min	Мах	
t _{PD}	А	Y	1.0	9.9	0.7	5.5	0.7	4.6	0.7	4.4	ns

 T_A = -40°C to +85°C, C_L = 30 or 50pF as noted (See Figure 2)

Parameter		To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
	Input		Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	А	Y	1.0	11	0.7	6.5	0.7	5.5	0.7	5	ns

 T_A = -40°C to +125°C, C_L = 15 pF as noted (See Figure 1)

Parameter	From Input	To Output	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	А	Y	1.0	12.5	0.7	7.5	0.7	6.5	0.7	5.5	ns

 $T_A = -40^{\circ}C$ to $+125^{\circ}C$, $C_L = 30$ or 50pF as noted (See Figure 2)

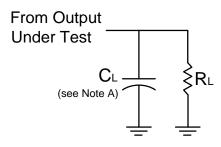
Parameter	From Input C	То	V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V		Unit
		Output	Min	Max	Min	Max	Min	Max	Min	Max	
t _{PD}	А	Y	1.0	14.0	0.7	8.5	0.7	7.0	0.7	6.5	ns



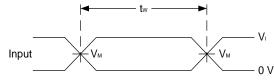
Operating Characteristics

T _A = +25°C							
	Parameter	Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{PD}	Power Dissipation Capacitance	f = 10 MHz	20	22	23	25	pF

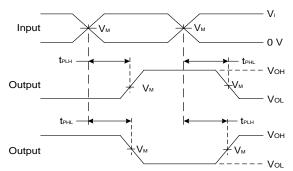
Parameter Measurement Information



V	Inputs		V	6	Р
V _{CC}	VI	t _R /t _F	V _M	C∟	RL
1.8V±0.15V	Vcc	≤2ns	V _{CC} /2	15pF	1ΜΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	15pF	1ΜΩ



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

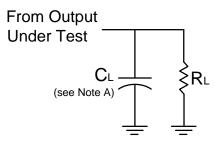
Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

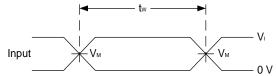
- B. All pulses are supplied at pulse repetition rate ≤ 10MHz.
 C. Inputs are measured separately one transition per measurement.
- D. tPLH and tPHL are the same as tPD.



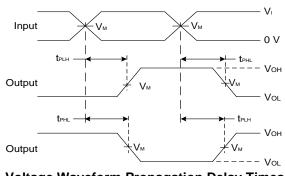
Parameter Measurement Information (Continued)



v	Inputs		N	0	D
Vcc	VI	t _R /t _F	V _M	C∟	RL
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1kΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

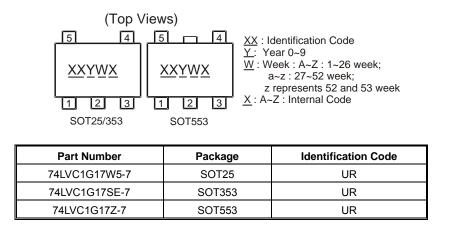
Figure 2. Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. tPLH and tPHL are the same as tPD.

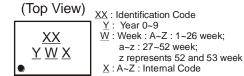


Marking Information

(1) SOT25, SOT353 and SOT553



(2) DFN packages



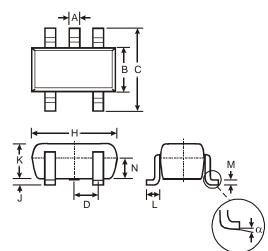
Package Part Number **Identification Code** 74LVC1G17FS3-7 X2-DFN0808-4 WR 74LVC1G17FW5-7 X1-DFN1010-6 V9 UR 74LVC1G17FW4-7 X2-DFN1010-6 74LVC1G17FX4-7 X2-DFN1409-6 MH 74LVC1G17FZ4-7 X2-DFN1410-6 UR



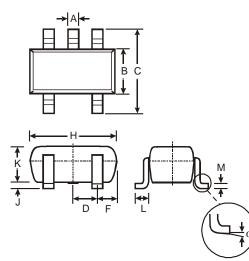
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

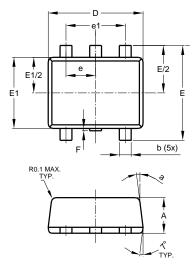
(1) Package Type: SOT25

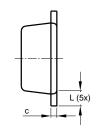


(2) Package Type: SOT353



(3) Package Type: SOT553





	SOT25				
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D			0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
Κ	1.00	1.30	1.10		
L	0.35	0.55	0.40		
Μ	0.10	0.20	0.15		
Ν	0.70	0.80	0.75		
α	0°	8°	_		
All D	imensi	ons in	mm		

	SOT353	
Dim	Min	Max
Α	0.10	0.30
в	1.15	1.35
с	2.00	2.20
D	0.65	Тур
F	0.40	0.45
H	1.80	2.20
J	0	0.10
ĸ	0.90	1.00
L	0.25	0.40
М	0.10	0.22
α	0°	8°
All Di	mensions	in mm

	SOT553				
Dim	Min	Max	Тур		
Α	0.55	0.62	0.60		
b	0.15	0.30	0.20		
c	0.10	0.18	0.15		
D	1.50	1.70	1.60		
ш	1.55	1.70	1.60		
E1	1.10	1.25	1.20		
е	0	.50 BS0	C		
e1	1	.00 BS0	0		
F	0.00	0.10			
L	0.10	0.30	0.20		
а	6°	8°	7°		
All	Dimens	ions in	mm		

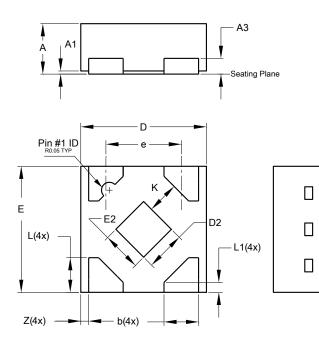
74LVC1G17 Document number: DS35124 Rev. 5 - 2 Downloaded from Arrow.com.



Package Outline Dimensions (Continued)

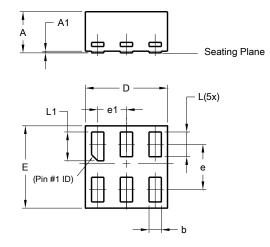
Please see http://www.diodes.com/package-outlines.html for the latest version.

(4) Package Type X2-DFN0808-4



	X2-DFN0808-4				
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
Е	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
к	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
Z	-	-	0.05		
A	II Dimens	sions in I	nm		

(5) Package Type: X1-DFN1010-6

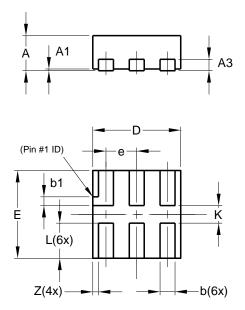


	X1-DFN1010-6				
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	1	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
E	0.95	1.050	1.00		
е		0.55 BSC			
e1		0.35 B	SC		
L	0.27	0.35	0.30		
L1	0.32	0.40	0.35		
All	Dimen	sions	in mm		

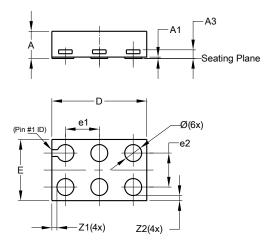


Package Outline Dimensions (Cont.)

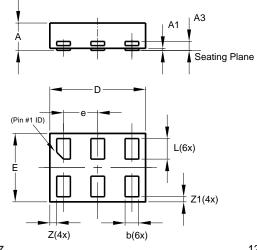
(6) Package Type X2-DFN1010-6



(7) Package Type: X2-DFN1409-6 6 (Chip Scale Alternative)



(8) Package Type: X2-DFN1410-6



	X2-DFN1010-6				
Dim	Min	Max	Тур		
Α		0.40	0.39		
A1	0.00	0.05	0.02		
A3	_		0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
Е	0.95	1.05	1.00		
е			0.35		
L	0.35	0.45	0.40		
κ	0.15				
Z			0.065		
All	Dimens	ions in	mm		

	X2-DFN1409-6				
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.13		
ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	-	-	0.50		
Z1	-	-	0.075		
Z2	-	-	0.075		
All	Dimens	ions in	mm		

	X2-DFN1410-6				
Dim	Min	Max	Тур		
Α		0.40	0.39		
A1	0.00	0.05	0.02		
A3			0.13		
b	0.15	0.25	0.20		
D	1.35	1.45	1.40		
Е	0.95	1.05	1.00		
е			0.50		
L	0.25	0.35	0.30		
Ζ	_	_	0.10		
Z1	0.045	0.105	0.075		
All	Dimens	ions in	mm		

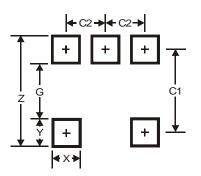
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Suggested Pad Layout

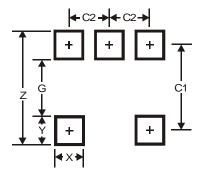
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SOT25



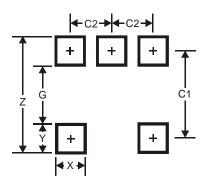
Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

(2) Package Type: SOT353



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(3) Package Type: SOT553



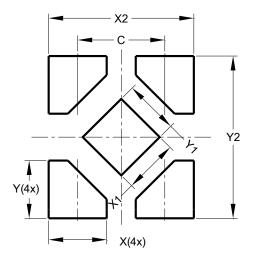
Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



Suggested Pad Layout (Continued)

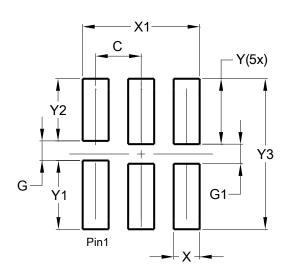
Please see http://www.diodes.com/package-outlines.html for the latest version.

(4) Package Type X2-DFN0808-4



Dimensions	Value (in mm)
С	0.480
Х	0.320
X1	0.300
X2	0.800
Y	0.320
Y1	0.300
Y2	0.900

(5) Package Type X1-DFN1010-6



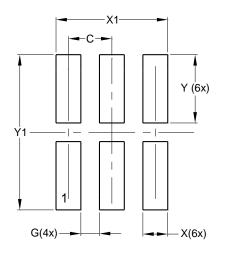
Dimensions	Value (in mm)
С	0.350
G	0.150
G1	0.150
Х	0.200
X1	0.900
Ŷ	0.500
Y1	0.525
Y2	0.475
Y3	1.150



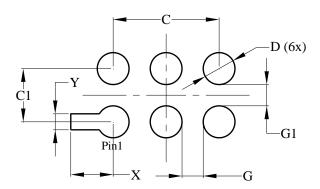
Suggested Pad Layout (Cont.)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(6) Package Type X2-DFN1010-6



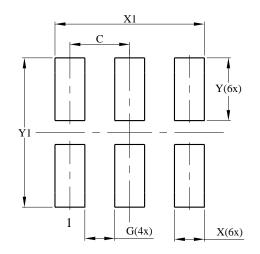
(7) Package Type: X2-DFN1409-6 (Chip Scale Alternative)



Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250

Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
х	0.400
Y	0.150

(8) Package Type: X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250

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